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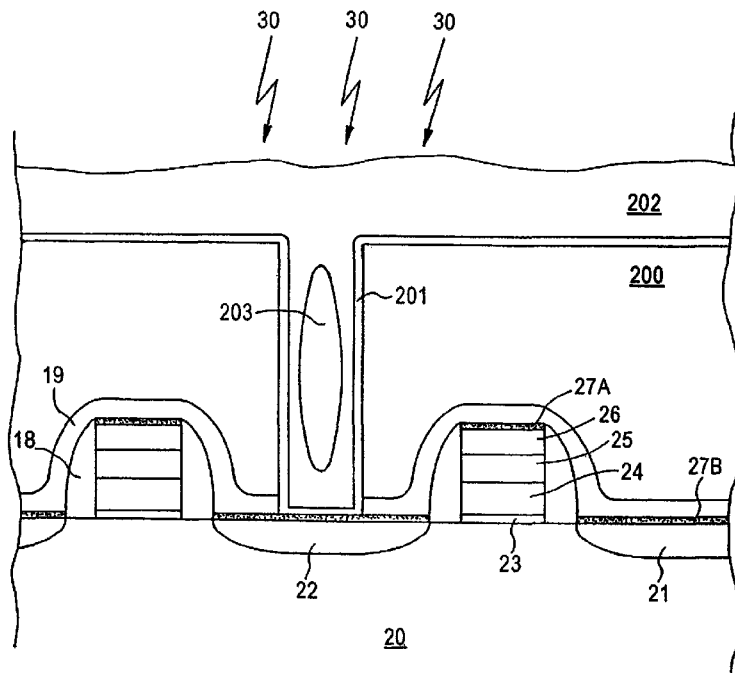
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(54) Title: METHOD OF ELIMINATING VOIDS IN W PLUGS



(57) Abstract: Reliable contacts/vias are formed by filling an opening in a dielectric layer (200) with W (202) and laser thermal annealing (30) to eliminate or significantly reduce voids (203). Embodiments include depositing W (202) to fill a contact/via opening in an interlayer dielectric (200), laser thermal annealing (30) in N₂ to elevate the temperature of the W filling the contact/via opening and reflow the W thereby eliminating voids (203). Embodiments include conducting CMP either before or subsequent to laser thermal annealing.



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